

ELECTRONIC DEVICES & CIRCUITS

(Common to EEE, ECE and EIE)

Time: 3 hours

Max. Marks: 70

PART - A
(Compulsory Question)

- 1 Answer the following: (10 X 02 = 20 Marks)
- Define forbidden energy gap.
 - Define peak inverse voltage of diode.
 - When does a transistor act as a switch?
 - Define transconductance.
 - What is operating point?
 - Which is the most commonly used transistor configuration. Why?
 - Write the voltage and current equation for hybrid parameters.
 - What is the significance of h-parameters?
 - What are the limitations of LCD?
 - Define radiant intensity for LED.

PART - B
(Answer all five units, 5 X 10 = 50 Marks)**UNIT - I**

- 2 (a) Derive the diode current equation?
(b) Describe the physical mechanism for avalanche breakdown.

OR

- 3 Derive the ripple factor and efficiency for full wave rectifier with input capacitance.

UNIT - II

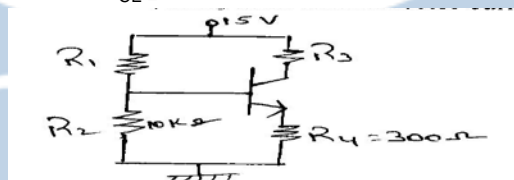
- 4 With the help of a neat diagram show different current components in a transistor.

OR

- 5 Draw and explain the drain characteristics of N-channel Enhancement type MOSFET.

UNIT - III

- 6 In the circuit show in figure transistor has $\beta = 100$ and $V_{BE(Active)} = 0.6$ V. Calculate the values of R_1 & R_3 Such that collector current of 1 mA and $V_{CE} = 2.5$ V.



OR

- 7 For the improvement of stability of the operating point what suggestions you would like to give for self-bias. Discuss with the help of stability factors.

UNIT - IV

- 8 (a) State Miller's theorem with the aid of a circuit diagram.
(b) Explain the dual of Miller's theorem.

OR

- 9 Given $I_E = 2.5$ mA, $h_{fe} = 140$, $h_{oe} = 20$ μ s and $h_{ob} = 0.5$ μ s determine:
(a) The common-emitter hybrid equivalent circuit.
(b) The common base r_e model.

UNIT - V

- 10 Sketch and explain the volt-ampere characteristics of a tunnel diode. Indicate the negative resistance portion.

OR

- 11 (a) Explain the construction and working of photo diode.
(b) Explain Schottky diode with necessary sketches.
